

Structural and Spin Polarization Effects of Cr, Fe and Ti Elements on Electronical Properties of α -Al₂O₃ by First Principle Calculations

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Abstract

Structural and spin polarization effects of Cr, Fe and Ti elements on electronical properties of alumina have been studied by using of Local spin density approximation within density functional theory. The calculated results indicated that substituting aluminium atoms by these dopants have a significant influence on the structural and electronic properties of α -Al₂O₃ crystals. Band gap of alumina decreases with the substitution of these impurities. Results show that band gap is different for spin-up and down (spin splitting effect). Among these impurities the effect of Ti on size of the energy gap is small in comparison with Cr and Fe. It is suggested that the origin of electrons spin splitting is appeared from exchange energy of d-states. These results may be useful to obtain a physical behaviour of transition metals for electrons spin polarization in d-states.

Keywords: LSDA, Spin Polarization, Alumina, Transition Metals

1. Introduction

A unique combination of alumina with transition metals is very important due to their possible industrial applications. The corundum or sapphire phase of alumina (α -Al₂O₃) has widespread applications in ceramic and semiconductor industry [1]. In order to improve electrical and optical properties of alumina, it can be doped by other metals; this requires the variation of electrical properties by theoretical calculations. Good substitutions on the Al atom sites are transition metals (TM), because the d-bands in these metals are partially filled and extended over the band gap. The substitutions of these metals change the band gap size and improve alumina properties.

Nearly all atoms have multiple electrons but most of them are paired up with another opposite spin electrons in the orbital. Solid magnetic properties are derived from the ground state properties of incompletely filled electron shells. Observed magnetic response, in a particular system largely depends on how the spin and orbital properties of these electrons end up in consideration of Pauli's exclusion principle and minimizing Coulomb repulsion [2].

In this work, the influence of spin polarization Cr, Fe and Ti elements on electrical properties of alumina have

been studied. Spin polarization is the first rule of Hund for determining the ground state (lowest energy) of electronic configuration in an atom. According to these rules and Pauli's exclusion principle, electrons have been arranged in a way to have maximum total spin, S. In fact, these minimize Coulomb energy so that two parallel spins can not be in the same state. Energy decreasing due to the preference of being parallel spins is called exchange energy. In solids, depending on whether the crystal is insulating or conducting, magnetism has historically been approached from two different schools of thinking: either a localized or itinerant point of view. In the localized concept of magnetism, the electrons and their magnetic properties remain associated with their respective paramagnetic ion in an insulating crystal. Conversely, in the itinerant picture, the conduction electrons are responsible for magnetism. The magnetic of ordering may arise based on the specific alignment of the atomic magnetic moments, favoured by atomic exchange interactions and itinerant magnetism which is associated with metallic behaviour.

Normally, in a metal, there is an equal number of spin-up and spin-down electrons which fill up states to the Fermi energy. In the absence of an external field, a stable

Table 1. Calculated lattice constants for α -Al₂O₃ and α -Al_{2-x}T_xO₃ (T: Cr, Fe, Ti; x=0.5).

Compositions	This work(Å)	Others(Exp., Å)
α -Al ₂ O ₃	A = b = 4.75699 C = 12.98769	a = b = 4.765 [5] c = 13.001
α -Al _{1.5} Cr _{0.5} O ₃	a = b = 4.75899 c = 12.97680	---
α -Al _{1.5} Fe _{0.5} O ₃	a = b = 4.75852 C = 12.97936	---
α -Al _{1.5} Ti _{0.5} O ₃	a = b = 4.76453 C = 12.94666	---

constant. Symmetric direction for calculation of band structure in the first brillouin zone of α -Al₂O₃ and α -Al_{2-x}T_xO₃ (T: Cr, Fe, Ti; x = 0.5) is shown in **Figure 3**.

Energy zero was set at the top of valance band. Energy scale is in eV and the origin of energy was arbitrarily set to be at the maximum valance band. The calculated band structures and densities of states of α -Al₂O₃ are shown in **Figure 4**. Focusing on α -Al₂O₃, the bands with the widths 0 - 7 eV and 16-18.5 below the Fermi level are due to O 2p and 2s states. Al 3p and 3s states are appeared above the Fermi level in conduction band. The distance between the maximum of the conduction band and the minimum of the valance band (at the Γ point) will be denoted as band gap (E_g). There are a large number of localized states at the top of the valance band. These states are originating mainly from the O 2p atom. The valance band edges near the Fermi energy for O atom are quite sharp, while the conduction band edges near the Fermi energy are not. The valance band is composed of the O-2p orbital hybridized with the Al-3s, 3p and 3d orbitals. The lower valance is formed predominantly by O 2s atom. The contribution of Al 3d and Al 3p in the valance band are rather small.

A band gap of ~6.33 eV (without empirical correction factor) was obtained for α -Al₂O₃. That is fairly closed to experimental values. For comparison, the band gap results obtained from experimental measurements and other theoretical methods have been summarized in **Table 2**. It can be seen that our results agree qualitatively with experimental results. There is also a well agreement with the other theoretical calculations.

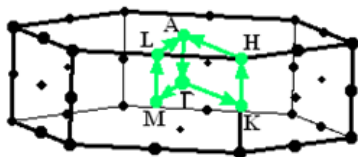


Figure 3. Considered symmetric direction in first brillouin zone for calculation of band structure of α -Al₂O₃ and α -Al_{2-x}T_xO₃ (T: Cr, Fe, Ti; x = 0.5).

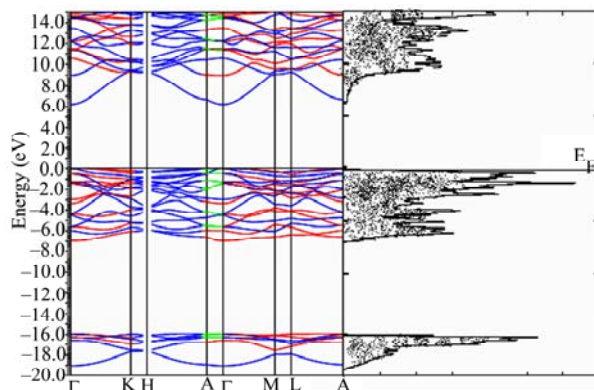


Figure 4. Calculated density of states and band structure for α -Al₂O₃.

Table 2. Obtained band gaps for Al₂O₃ by various methods.

Methods	Band gap (eV)
Experimental	
α -Al ₂ O ₃ [6]	~10.8
α -Al ₂ O ₃ [7]	~8.8
Amorphous alumina [8]	~8.7
Theory(LDA)	
κ -Al ₂ O ₃ [9]	~5.3
α -Al ₂ O ₃ [10]	~6.2
α -Al ₂ O ₃ (this work)	~6.33

The calculated electronic band structure and density of states of α -Al_{1.5}Cr_{0.5}O₃, α -Al_{1.5}Fe_{0.5}O₃ and α -Al_{1.5}Ti_{0.5}O₃ are shown in **Figures 5-7**. By comparing **Figure 4** and **Figures 5-7**, it can be seen that the substitution of Cr, Fe and Ti for Al in α -Al₂O₃ structure results in reducing the band gap. The band gap decreases mainly due to Cr, Fe and Ti-d state in the conduction band in different energies.

The obtained results from **Figures 5-7**, show that for all compositions, the energy gaps are smaller for spin-up states than spin-down. Therefore, electrical properties are different for both states and they can be applicable in spintronic devices. As can be seen in **Table 3**, among these impurities the effect of Ti on size of the energy gap is smaller in comparison with Cr and Fe. These are related to exchange energy splitting of d-states and magnetic properties of these materials.

4. Conclusions

The results of obtained show that the alumina energy gap was decreased by substitution of Cr, Fe and Ti impurities on the Al sites in α -Al₂O₃. It was found that energy gaps were different for spin-up and spin-down states for all α -Al_{2-x}T_xO₃ (T: Cr, Fe, Ti; x=0.5) compositions. Therefore, electrical properties are depended on spin polarization of electrons. Spin splitting effect were appeared from

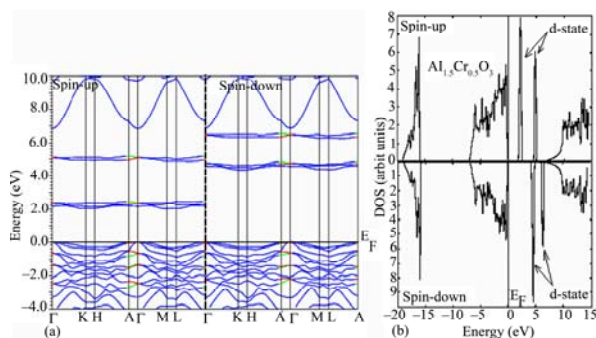


Figure 5. (a) Band structure of $\alpha\text{-Al}_{1.5}\text{Cr}_{0.5}\text{O}_3$ (b) Density of states for $\alpha\text{-Al}_{1.5}\text{Cr}_{0.5}\text{O}_3$.

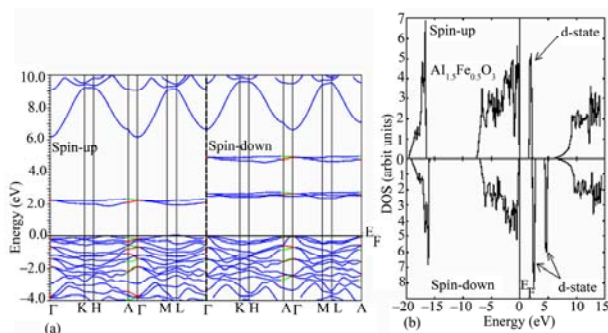


Figure 6. (a) Band structure of $\alpha\text{-Al}_{1.5}\text{Fe}_{0.5}\text{O}_3$. (b) Density of states for $\alpha\text{-Al}_{1.5}\text{Fe}_{0.5}\text{O}_3$.

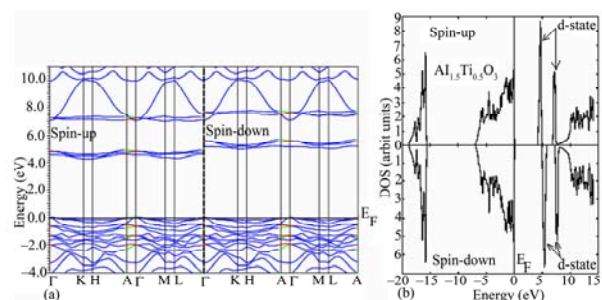


Figure 7. (a) Band structure of $\alpha\text{-Al}_{1.5}\text{Ti}_{0.5}\text{O}_3$. (b) Density of states for $\alpha\text{-Al}_{1.5}\text{Ti}_{0.5}\text{O}_3$.

Table 3. Obtained band gap for $\alpha\text{-Al}_2\text{O}_3$ and $\alpha\text{-Al}_{2-x}\text{T}_x\text{O}_3$ (T: Cr, Fe, Ti; $x = 0.5$) in spin-up and down states.

Compositions	Band gape (eV)	
	Spin-up	Spin-down
$\alpha\text{-Al}_2\text{O}_3$		6.33
$\alpha\text{-Al}_{1.5}\text{Cr}_{0.5}\text{O}_3$	1.77	4.13
$\alpha\text{-Al}_{1.5}\text{Fe}_{0.5}\text{O}_3$	1.56	2.04
$\alpha\text{-Al}_{1.5}\text{Ti}_{0.5}\text{O}_3$	4.13	4.94

exchange interaction among the electrons in d-states. These results may be useful to obtain a physical picture of electrons spin polarization in d-states of transition metals. Among these impurities, the Cr element has the stronger spin splitting effect than the other impurities (Fe and Ti) in Alumina.

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6. References

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